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By: Sam Pongoti Date: 12/9/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Lothar Risch et al.  
Applic. No. : 09/996,279  
Filed : November 28, 2001  
Title : Double Gate MOSFET Transistor and Method for the Production Thereof  
Examiner : Shrinivas H. Rao  
Group Art Unit : 2814

A M E N D M E N T

Hon. Commissioner of Patents and Trademarks,  
Washington, D. C. 20231

Sir :

Responsive to the Office action dated August 9, 2002 kindly  
amend the above-identified application as follows:

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DEC 19 2002  
TECHNOLOGY CENTER 2800

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*Mr Lothar Ralph*